

A²
Sub B₁
10. (Amended) The method of reproducing a mark on a semiconductor wafer according to claim 2, wherein the predetermined mark is formed by means of a combination of dots, each dot measuring μm wide, and is affixed on the interior wall surface of a notch, and the substantially-effaced mark is reproduced by means of forming a mark essentially identical with the substantially-effaced mark at another location in the vicinity of the substantially-effaced mark.

11. (Amended) The method of reproducing a mark on a semiconductor wafer according to claim 2, wherein the predetermined mark is an ID mark which is assigned to the semiconductor wafer, is formed by means of a combination of dots, each dot measuring μm wide, and is affixed on the interior wall surface of a notch, and the substantially-effaced mark is reproduced by means of forming a mark essentially identical with the substantially-effaced mark at another location in the vicinity of the substantially-effaced mark.

Sub B₁
A³
17. (Amended) The semiconductor wafer for distribution purpose according to claim 12, wherein two or more essentially-identical marks are formed by means of a combination of dots, each dot measuring μm wide, and some of two or more essentially-identical marks are provided on the front side of the semiconductor wafer and the other essentially-identical marks are provided on the reverse side of the same, such that the marks undergo the same surface treatment at different speeds during the course of manufacture and such that the marks are located within an area where a single optical reading machine can read the marks simultaneously.

18. (Amended) The semiconductor wafer for distribution purpose according to claim 12, wherein two or more essentially-identical marks are minute ID marks which are assigned to the semiconductor wafer and are formed by means of a combination of dots, each dot measuring μm wide, and some of two or more essentially-identical marks are provided on the front side of the semiconductor wafer and the other essentially-identical marks are provided on the reverse side of the same, such that the marks undergo the same surface treatment at different speeds during the course of manufacture and such that the marks are located within an area where a single optical reading machine can read the marks simultaneously.

19. (Amended) The semiconductor wafer for distribution purpose according to claim 12, wherein two or more essentially-identical marks are minute ID marks which are assigned to the

semiconductor wafer, are formed by means of a combination of dots, each dot measuring 1 to 13 μm wide, and are affixed on the interior wall surface of a notch, and some of two or more essentially-identical marks are provided on the front side of the semiconductor wafer and the other essentially-identical marks are provided on the reverse side of the same, such that the marks undergo the same surface treatment at different speeds during the course of manufacture and such that the marks are located within an area where a single optical reading machine can read the marks simultaneously.

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20. (Amended) The semiconductor wafer for distribution purpose according to claim 12, wherein two or more essentially-identical marks are formed by means of a combination of dots, each dot measuring 1 to 13 μm wide, for positioning purpose, and some of two or more essentially-identical marks are provided on the front side of the semiconductor wafer and the other essentially-identical marks are provided on the reverse side of the same, such that the marks undergo the same surface treatment at different speeds during the course of manufacture and such that the marks are located within an area where a single optical reading machine can read the marks simultaneously.

21. (Amended) The semiconductor wafer for distribution purpose according to claim 12, wherein two or more essentially-identical marks are formed by means of a combination of dots, each dot measuring μm wide and indicate crystal orientation of the semiconductor wafer, and some of two or more essentially-identical marks are provided on the front side of the semiconductor wafer and the other essentially-identical marks are provided on the reverse side of the same, such that the marks undergo the same surface treatment at different speeds during the course of manufacture and such that the marks are located within an area where a single optical reading machine can read the marks simultaneously.

22. (Amended) The semiconductor wafer for distribution purpose according to claim 12, wherein the semiconductor wafer is perfectly annular; two or more essentially-identical marks are formed by means of a combination of dots, each dot measuring μm wide, at least one of the two or more essentially-identical marks are provided on the front side of the semiconductor wafer and the other essentially-identical marks are provided on the reverse side of the same, such that the marks undergo the same surface treatment at different speeds during the course of manufacture and such that the marks are located within an area where a single optical reading machine can read the marks simultaneously.